

MEMORY

CMOS

2 M × 8 BIT

FAST PAGE MODE DYNAMIC RAM

MB81V17800B-50/-60/-50L/-60L

CMOS 2,097,152 × 8 Bit Fast Page Mode Dynamic RAM

■ DESCRIPTION

The Fujitsu MB81V17800B is a fully decoded CMOS Dynamic RAM (DRAM) that contains 16,777,216 memory cells accessible in 8-bit increments. The MB81V17800B features a “fast page” mode of operation whereby high-speed random access of up to 1,024 × 8 bits of data within the same row can be selected. The MB81V17800B DRAM is ideally suited for mainframe, buffers, hand-held computers video imaging equipment, and other memory applications where very low power dissipation and high bandwidth are basic requirements of the design. Since the standby current of the MB81V17800B is very small, the device can be used as a non-volatile memory in equipment that uses batteries for primary and/or auxiliary power.

The MB81V17800B is fabricated using silicon gate CMOS and Fujitsu’s advanced four-layer polysilicon and two-layer aluminum process. This process, coupled with advanced stacked capacitor memory cells, reduces the possibility of soft errors and extends the time interval between memory refreshes. Clock timing requirements for the MB81V17800B are not critical and all inputs are LVTTTL compatible.

■ PRODUCT LINE & FEATURES

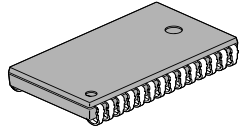
Parameter		MB81V17800B				
		-50	-50L	-60	-60L	
RAS Access Time		50 ns max.		60 ns max.		
Random Cycle Time		90 ns min.		110 ns min.		
Address Access Time		25 ns max.		30 ns max.		
CAS Access Time		13 ns max.		15 ns max.		
Fast Page Mode Cycle Time		35 ns min.		40 ns min.		
Low Power Dissipation	Operating Current	468 mW max.		396 mW max.		
	Standby Current	LVTTTL level	3.6 mW max.	3.6 mW max.	3.6 mW max.	3.6 mW max.
		CMOS level	1.8 mW max.	0.54 mW max.	1.8 mW max.	0.54 mW max.

- 2,097,152 words × 8 bit organization
- Silicon gate, CMOS, Advanced Capacitor Cell
- All input and output are LVTTTL compatible
- 2048 refresh cycles every 32.8 ms
- Self refresh function (Low power version)
- Early write or \overline{OE} controlled write capability
- RAS only, \overline{CAS} -before-RAS, or Hidden Refresh
- Fast page mode, Read-Modify-Write capability
- On chip substrate bias generator for high performance
- Standard and low power versions

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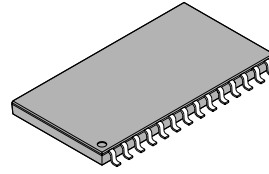
■ PACKAGE

28-pin plastic SOJ



(LCC-28P-M07)

28-pin plastic TSOP (II)



(FPT-28P-M14)
(Normal Bend)

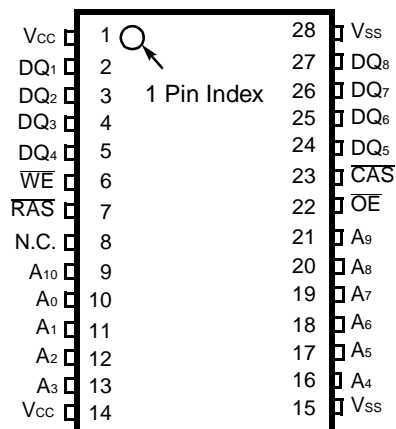
Package and Ordering Information

- 28-pin plastic (400 mil) SOJ, order as MB81V17800B-xxPJ
- 28-pin plastic (400 mil) TSOP-II with normal bend leads, order as MB81V17800B-xxPFTN and MB81V17800B-xxLPFTN (Low Power)

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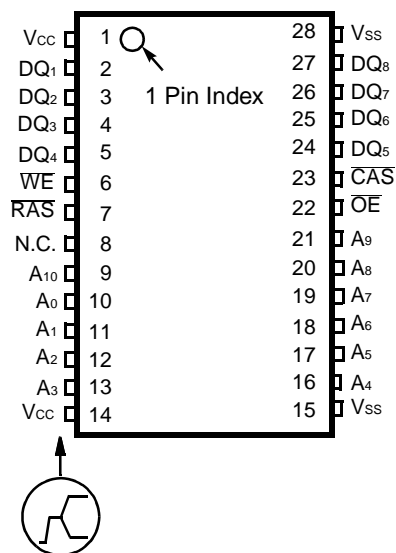
■ PIN ASSIGNMENTS AND DESCRIPTIONS

28-Pin SOJ
(TOP VIEW)
<LCC-28P-M07>



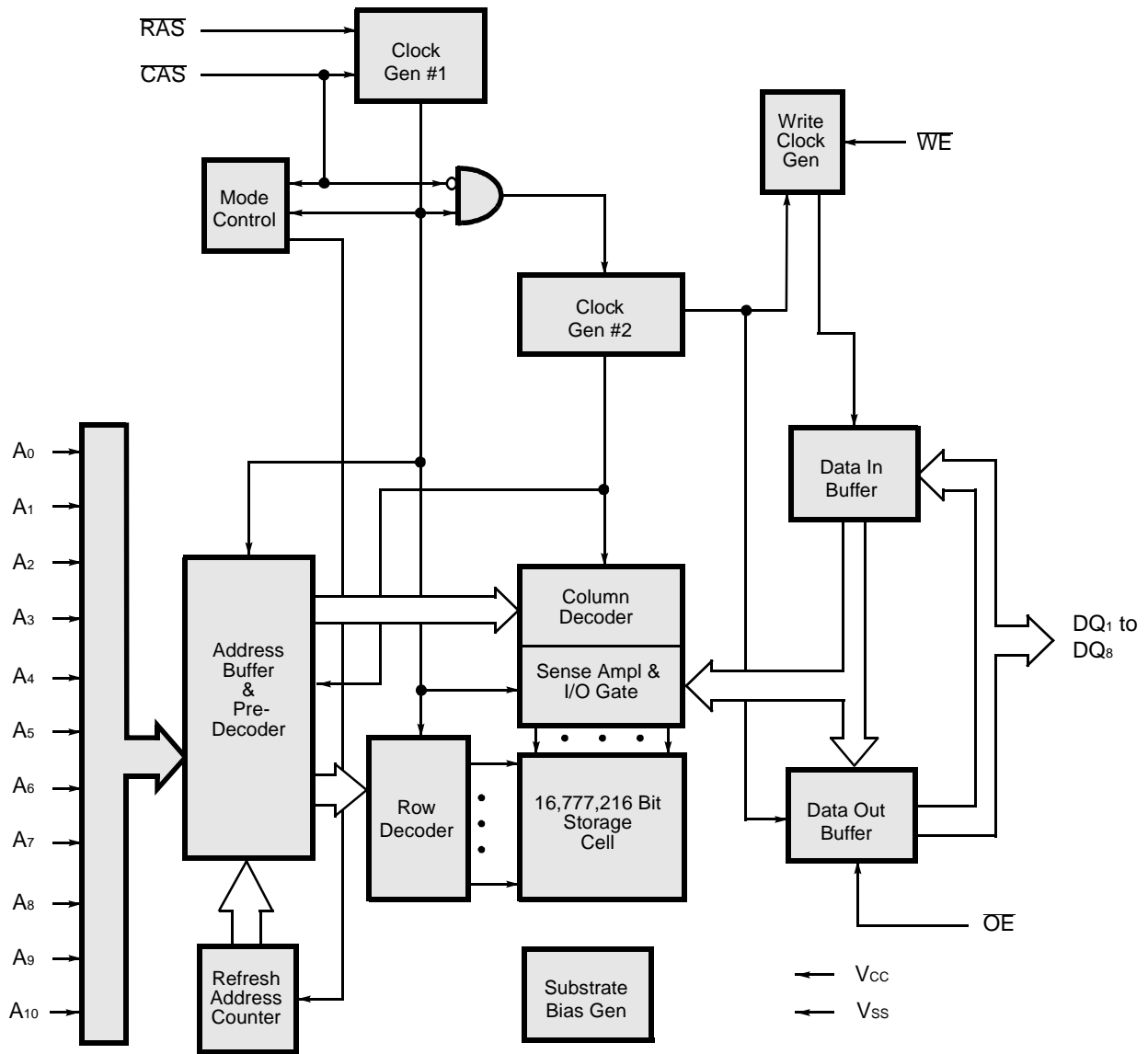
Designator	Function
A ₀ to A ₁₀	Address inputs row : A ₀ to A ₁₀ column : A ₀ to A ₉ refresh : A ₀ to A ₁₀
RAS	Row address strobe
CAS	Column address strobe
WE	Write enable
OE	Output enable
DQ ₁ to DQ ₈	Data Input/Output
V _{CC}	+3.3 volt power supply
V _{SS}	Circuit ground

28-Pin TSOP (II)
(TOP VIEW)
<Normal Bend: LCC-28P-M14>



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Fig. 1 - MB81V17800B DYNAMIC RAM - BLOCK DIAGRAM



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FUNCTIONAL TRUTH TABLE

Operation Mode	Clock Input				Address Input		Input Data		Refresh	Note
	RAS	CAS	WE	OE	Row	Column	Input	Output		
Standby	H	H	X	X	—	—	—	High-Z	—	
Read Cycle	L	L	H	L	Valid	Valid	—	Valid	Yes*	$t_{RCS} \geq t_{RCS}(\text{min})$
Write Cycle (Early Write)	L	L	L	X	Valid	Valid	Valid	High-Z	Yes*	$t_{WCS} \geq t_{WCS}(\text{min})$
Read-Modify- Write Cycle	L	L	H→L	L→H	Valid	Valid	Valid	Valid	Yes*	
RAS-only Refresh Cycle	L	H	X	X	Valid	X	—	High-Z	Yes	
CAS-before-RAS Refresh Cycle	L	L	H	X	X	X	—	High-Z	Yes	$t_{CSR} \geq t_{CSR}(\text{min})$
Hidden Refresh Cycle	H→L	L	H→X	L	X	X	—	Valid	Yes	Previous data is kept.

X : "H" or "L"

* : It is impossible in Fast Page Mode.

FUNCTIONAL OPERATION

ADDRESS INPUTS

Twenty-one input bits are required to decode any eight of 16,777,216 cell addresses in the memory matrix. Since only eleven address bits (A_0 to A_{10}) are available, the row and column inputs are separately strobed by $\overline{\text{RAS}}$ and $\overline{\text{CAS}}$ as shown in Figure 1. First, eleven row address bits are input on pins A_0 -through- A_{10} and latched with the row address strobe ($\overline{\text{RAS}}$) then, ten column address bits are input and latched with the column address strobe ($\overline{\text{CAS}}$). Both row and column addresses must be stable on or before the falling edge of $\overline{\text{RAS}}$ and $\overline{\text{CAS}}$, respectively. The address latches are of the flow-through type; thus, address information appearing after $t_{\text{RAH}}(\text{min}) + t_{\text{t}}$ is automatically treated as the column address.

WRITE ENABLE

The read or write mode is determined by the logic state of $\overline{\text{WE}}$. When $\overline{\text{WE}}$ is active Low, a write cycle is initiated; when $\overline{\text{WE}}$ is High, a read cycle is selected. During the read mode, input data is ignored.

DATA INPUTS

Input data is written into memory in either of three basic ways—an early write cycle, an $\overline{\text{OE}}$ (delayed) write cycle, and a read-modify-write cycle. The falling edge of $\overline{\text{WE}}$ or $\overline{\text{CAS}}$, whichever is later, serves as the input data-latch strobe. In an early write cycle, the input data (DQ_1 to DQ_8) is strobed by $\overline{\text{CAS}}$ and the setup/hold times are referenced to $\overline{\text{CAS}}$ because $\overline{\text{WE}}$ goes Low before $\overline{\text{CAS}}$. In a delayed write or a read-modify-write cycle, $\overline{\text{WE}}$ goes Low after $\overline{\text{CAS}}$; thus, input data is strobed by $\overline{\text{WE}}$ and all setup/hold times are referenced to the write-enable signal.

DATA OUTPUTS

The three-state buffers are LVTTTL compatible with a fanout of one TTL loads. Polarity of the output data is identical to that of the input; the output buffers remain in the high-impedance state until the column address strobe goes Low. When a read or read-modify-write cycle is executed, valid outputs are obtained under the following conditions:

- t_{RAC} : from the falling edge of $\overline{\text{RAS}}$ when $t_{\text{RCD}}(\text{max})$ is satisfied.
- t_{CAC} : from the falling edge of $\overline{\text{CAS}}$ when t_{RCD} is greater than $t_{\text{RCD}}(\text{max})$.
- t_{AA} : from column address input when t_{RAD} is greater than $t_{\text{RAD}}(\text{max})$.
- t_{OEA} : from the falling edge of $\overline{\text{OE}}$ when $\overline{\text{OE}}$ is brought Low after t_{RAC} , t_{CAC} , or t_{AA} .

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The data remains valid until either $\overline{\text{CAS}}$ or $\overline{\text{OE}}$ returns to a High logic level. When an early write is executed, the output buffers remain in a high-impedance state during the entire cycle.

FAST PAGE MODE OF OPERATION

The fast page mode of operation provides faster memory access and lower power dissipation. The fast page mode is implemented by keeping the same row address and strobing in successive column addresses. To satisfy these conditions, $\overline{\text{RAS}}$ is held Low for all contiguous memory cycles in which row addresses are common. For each fast page of memory, any of $1,024 \times 8$ bits can be accessed and, when multiple MB81V17800Bs are used, $\overline{\text{CAS}}$ is decoded to select the desired memory fast page. Fast page mode operations need not be addressed sequentially and combinations of read, write, and/or read-modify-write cycles are permitted.

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■ ABSOLUTE MAXIMUM RATINGS (See WARNING)

Parameter	Symbol	Value	Unit
Voltage at Any Pin Relative to V_{SS}	V_{IN}, V_{OUT}	-0.5 to +4.6	V
Voltage of V_{CC} Supply Relative to V_{SS}	V_{CC}	-0.5 to +4.6	V
Power Dissipation	P_D	1.0	W
Short Circuit Output Current	—	-50 to +50	mA
Operating Temperature	T_{OPE}	0 to 70	°C
Storage Temperature	T_{STG}	-55 to +125	°C

WARNING: Semiconductor devices can be permanently damaged by application of stress (voltage, current, temperature, etc.) in excess of absolute maximum ratings. Do not exceed these ratings.

■ RECOMMENDED OPERATING CONDITIONS

Parameter	Notes	Symbol	Min.	Typ.	Max.	Unit	Ambient Operating Temp.
Supply Voltage	*1	V_{CC}	3.0	3.3	3.6	V	0°C to +70°C
		V_{SS}	0	0	0		
Input High Voltage, All Inputs	*1	V_{IH}	2.0	—	$V_{CC} + 0.3$	V	
Input Low Voltage, All Inputs/Outputs*	*1	V_{IL}	-0.3	—	0.8	V	

* : Undershoots of up to -2.0 volts with a pulse width not exceeding 20 ns are acceptable.

WARNING: Recommended operating conditions are normal operating ranges for the semiconductor device. All the device's electrical characteristics are warranted when operated within these ranges.

Always use semiconductor devices within the recommended operating conditions. Operation outside these ranges may adversely affect reliability and could result in device failure.

No warranty is made with respect to uses, operating conditions, or combinations not represented on the data sheet. Users considering application outside the listed conditions are advised to contact their FUJITSU representative beforehand.

■ CAPACITANCE

($T_A = 25^\circ\text{C}$, $f = 1\text{ MHz}$)

Parameter	Symbol	Typ.	Max.	Unit
Input Capacitance, A_0 to A_{10}	C_{IN1}	—	5	pF
Input Capacitance, \overline{RAS} , \overline{CAS} , \overline{WE} , \overline{OE}	C_{IN2}	—	5	pF
Input/Output Capacitance, DQ_1 to DQ_4	C_{DQ}	—	7	pF

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■ DC CHARACTERISTICS

(At recommended operating conditions unless otherwise noted.)

Note 3

Parameter	Notes	Symbol	Conditions	Values				Unit
				Min.	Typ.	Max.		
						Std power	Low power	
Output High Voltage		V_{OH}	$I_{OH} = -2.0 \text{ mA}$	2.4	—	—	—	V
Output Low Voltage		V_{OL}	$I_{OL} = 2.0 \text{ mA}$	—	—	0.4	0.4	
Input Leakage Current (Any Input)		$I_{I(L)}$	$0 \text{ V} \leq V_{IN} \leq V_{CC}$; $3.0 \text{ V} \leq V_{CC} \leq 3.6 \text{ V}$; $V_{SS} = 0 \text{ V}$; All other pins not under test = 0 V	-10	—	10	10	μA
Output Leakage Current		$I_{DO(L)}$	$0 \text{ V} \leq V_{OUT} \leq V_{CC}$; $3.0 \text{ V} \leq V_{CC} \leq 3.6 \text{ V}$; Data out disabled	-10	—	10	10	μA
Operating Current (Average Power Supply Current)	*2	MB81V17800B -50/50L	$\overline{\text{RAS}}$ & $\overline{\text{CAS}}$ cycling; $t_{RC} = \text{min}$	—	—	130	130	mA
		MB81V17800B -60/60L				110	110	
Standby Current (Power Supply Current)	*2	TTL level	$\overline{\text{RAS}} = \overline{\text{CAS}} = V_{IH}$	—	—	1.0	1.0	mA
		CMOS level	$\overline{\text{RAS}} = \overline{\text{CAS}} \geq V_{CC} - 0.2 \text{ V}$			500	150	
Refresh Current #1 (Average Power Supply Current)	*2	MB81V17800B -50/50L	$\overline{\text{CAS}} = V_{IH}$, $\overline{\text{RAS}}$ cycling; $t_{RC} = \text{min}$	—	—	130	130	mA
		MB81V17800B -60/60L				110	110	
Fast Page Mode Current	*2	MB81V17800B -50/50L	$\overline{\text{RAS}} = V_{IL}$, $\overline{\text{CAS}}$ cycling; $t_{RC} = \text{min}$	—	—	100	100	mA
		MB81V17800B -60/60L				90	90	
Refresh Current #2 (Average Power Supply Current)	*2	MB81V17800B -50/50L	$\overline{\text{RAS}}$ cycling; $\overline{\text{CAS}}$ -before- $\overline{\text{RAS}}$; $t_{RC} = \text{min}$	—	—	130	130	mA
		MB81V17800B -60/60L				110	110	
Battery Backup Current (Average Power Supply Current)	*2	MB81V17800B -50/60	$\overline{\text{RAS}}$ cycling; $\overline{\text{CAS}}$ -before- $\overline{\text{RAS}}$; $t_{RC} = 16 \mu\text{s}$ $t_{RAS} = \text{min. to } 300 \text{ ns}$ $V_{IH} \geq V_{CC} - 0.2 \text{ V}$, $V_{IL} \leq 0.2 \text{ V}$	—	—	1000	—	μA
		MB81V17800B -50L/60L	$\overline{\text{RAS}}$ cycling; $\overline{\text{CAS}}$ -before- $\overline{\text{RAS}}$; $t_{RC} = 64 \mu\text{s}$ $t_{RAS} = \text{min. to } 300 \text{ ns}$ $V_{IH} \geq V_{CC} - 0.2 \text{ V}$, $V_{IL} \leq 0.2 \text{ V}$			—	300	
Refresh Current#3 (Average Power Supply Current)		MB81V17800B -50L/60L	$\overline{\text{RAS}} = V_{IL}$, $\overline{\text{CAS}} = V_{IL}$ Self refresh;	—	—	—	250	μA

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■ AC CHARACTERISTICS

(At recommended operating conditions unless otherwise noted.)

Notes 3, 4, 5

No.	Parameter	Notes	Symbol	MB81V17800B-50/50L		MB81V17800B-60/60L		Unit
				Min.	Max.	Min.	Max.	
1	Time between Refresh	Std power	t _{REF}	—	32.8	—	32.8	ms
		Low power		—	128	—	128	
2	Random Read/Write Cycle Time		t _{RC}	90	—	110	—	ns
3	Read-Modify-Write Cycle Time		t _{RWC}	126	—	150	—	ns
4	Access Time from $\overline{\text{RAS}}$	*6,9	t _{RAC}	—	50	—	60	ns
5	Access Time from $\overline{\text{CAS}}$	*7,9	t _{CAC}	—	13	—	15	ns
6	Column Address Access Time	*8,9	t _{AA}	—	25	—	30	ns
7	Output Hold Time		t _{OH}	3	—	3	—	ns
8	Output Buffer Turn On Delay Time		t _{ON}	0	—	0	—	ns
9	Output Buffer Turn Off Delay Time	*10	t _{OFF}	—	13	—	15	ns
10	Transition Time		t _r	3	50	3	50	ns
11	$\overline{\text{RAS}}$ Precharge Time		t _{RP}	30	—	40	—	ns
12	$\overline{\text{RAS}}$ Pulse Width		t _{RAS}	50	100000	60	100000	ns
13	$\overline{\text{RAS}}$ Hold Time		t _{RSH}	13	—	15	—	ns
14	$\overline{\text{CAS}}$ to $\overline{\text{RAS}}$ Precharge Time		t _{CRP}	5	—	5	—	ns
15	$\overline{\text{RAS}}$ to $\overline{\text{CAS}}$ Delay Time	*11,12	t _{RCD}	17	37	20	45	ns
16	$\overline{\text{CAS}}$ Pulse Width		t _{CAS}	13	—	15	—	ns
17	$\overline{\text{CAS}}$ Hold Time		t _{CSH}	50	—	60	—	ns
18	$\overline{\text{CAS}}$ Precharge Time (Normal)	*19	t _{CPN}	7	—	10	—	ns
19	Row Address Setup Time		t _{ASR}	0	—	0	—	ns
20	Row Address Hold Time		t _{RAH}	7	—	10	—	ns
21	Column Address Setup Time		t _{ASC}	0	—	0	—	ns
22	Column Address Hold Time		t _{CAH}	7	—	10	—	ns
23	Column Address Hold Time from $\overline{\text{RAS}}$		t _{AR}	24	—	30	—	ns
24	$\overline{\text{RAS}}$ to Column Address Delay Time	*13	t _{RAD}	12	25	15	30	ns
25	Column Address to $\overline{\text{RAS}}$ Lead Time		t _{RAL}	25	—	30	—	ns
26	Column Address to $\overline{\text{CAS}}$ Lead Time		t _{CAL}	25	—	30	—	ns
27	Read Command and Setup Time		t _{RCS}	0	—	0	—	ns
28	Read Command Hold Time Referenced to $\overline{\text{RAS}}$	*14	t _{RRH}	0	—	0	—	ns
29	Read Command Hold Time Referenced to $\overline{\text{CAS}}$	*14	t _{RCH}	0	—	0	—	ns
30	Write Command Setup Time	*15	t _{WCS}	0	—	0	—	ns
31	Write Command Hold Time		t _{WCH}	7	—	10	—	ns
32	Write Command Hold Time from $\overline{\text{RAS}}$		t _{WCR}	24	—	30	—	ns

(Continued)

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(Continued)

No.	Parameter	Notes	Symbol	MB81V17800B-50/50L		MB81V17800B-60/60L		Unit
				Min.	Max.	Min.	Max.	
33	\overline{WE} Pulse Width		tWP	7	—	10	—	ns
34	Write Command to \overline{RAS} Lead Time		tRWL	13	—	15	—	ns
35	Write Command to \overline{CAS} Lead Time		tCWL	13	—	15	—	ns
36	DIN Setup Time		tDS	0	—	0	—	ns
37	DIN Hold Time		tDH	7	—	10	—	ns
38	Data Hold Time from \overline{RAS}		tDHR	24	—	30	—	ns
39	\overline{RAS} to \overline{WE} Delay Time	*20	tRWD	68	—	80	—	ns
40	\overline{CAS} to \overline{WE} Delay Time	*20	tCWD	31	—	35	—	ns
41	Column Address to \overline{WE} Delay Time	*20	tAWD	43	—	50	—	ns
42	\overline{RAS} Precharge Time to \overline{CAS} Active Time (Refresh cycles)		tRPC	5	—	5	—	ns
43	\overline{CAS} Setup Time for \overline{CAS} -before- \overline{RAS} Refresh		tCSR	0	—	0	—	ns
44	\overline{CAS} Hold Time for \overline{CAS} -before- \overline{RAS} Refresh		tCHR	10	—	10	—	ns
45	Access Time from \overline{OE}	*9	tOEA	—	13	—	15	ns
46	Output Buffer Turn Off Delay from \overline{OE}	*10	tOEZ	—	13	—	15	ns
47	\overline{OE} to \overline{RAS} Lead Time for Valid Data		tOEL	5	—	5	—	ns
48	\overline{OE} Hold Time Referenced to \overline{WE}	*16	tOEH	5	—	5	—	ns
49	\overline{OE} to Data In Delay Time		tOED	13	—	15	—	ns
50	\overline{CAS} to Data In Delay Time		tCDD	13	—	15	—	ns
51	DIN to \overline{CAS} Delay Time	*17	tDZC	0	—	0	—	ns
52	DIN to \overline{OE} Delay Time	*17	tDZO	0	—	0	—	ns
53	Fast Page Mode \overline{RAS} Pulse Width		tRASP	—	100000	—	100000	ns
54	Fast Page Mode Read/Write Cycle Time		tPC	35	—	40	—	ns
55	Fast Page Mode Read-Modify-Write Cycle Time		tPRWC	71	—	80	—	ns
56	Access Time from \overline{CAS} Precharge	*9,18	tCPA	—	30	—	35	ns
57	Fast Page Mode \overline{CAS} Precharge Time		tCP	7	—	10	—	ns
58	Fast Page Mode \overline{RAS} Hold Time from \overline{CAS} Precharge		tRHCP	30	—	35	—	ns
59	Fast Page Mode \overline{CAS} Precharge to \overline{WE} Delay Time	*20	tCPWD	48	—	55	—	ns

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- Notes:**
- *1. Referenced to V_{SS} .
 - *2. I_{CC} depends on the output load conditions and cycle rates; the specified values are obtained with the output open. I_{CC} depends on the number of address change as $\overline{RAS}=V_{IL}$, $\overline{CAS}=V_{IH}$ and $V_{IL} > -0.3$ V. I_{CC1} , I_{CC3} , I_{CC4} and I_{CC5} are specified at one time of address change during $\overline{RAS}=V_{IL}$ and $\overline{CAS}=V_{IH}$. I_{CC2} is specified during $\overline{RAS}=V_{IH}$ and $V_{IL} > -0.3$ V. I_{CC6} is measured on condition that all address signals are fixed steady state.
 - *3. An initial pause ($\overline{RAS}=\overline{CAS}=V_{IH}$) of 200 μ s is required after power-up followed by any eight \overline{RAS} -only cycles before proper device operation is achieved. In case of using internal refresh counter, a minimum of eight \overline{CAS} -before- \overline{RAS} initialization cycles instead of 8 \overline{RAS} cycles are required.
 - *4. AC characteristics assume $t_T = 5$ ns.
 - *5. V_{IH} (min) and V_{IL} (max) are reference levels for measuring timing of input signals. Also transition times are measured between V_{IH} (min) and V_{IL} (max).
The output reference levels are $V_{OH} = 2.0$ V and $V_{OL} = 0.8$ V.
 - *6. Assumes that $t_{RCD} \leq t_{RCD}(\max)$, $t_{RAD} \leq t_{RAD}(\max)$. If t_{RCD} is greater than the maximum recommended value shown in this table, t_{RAC} will be increased by the amount that t_{RCD} exceeds the value shown. Refer to Fig. 2 and 3.
 - *7. If $t_{RCD} \geq t_{RCD}(\max)$, $t_{RAD} \geq t_{RAD}(\max)$, and $t_{ASC} \geq t_{AA} - t_{CAC} - t_T$, access time is t_{CAC} .
 - *8. If $t_{RAD} \geq t_{RAD}(\max)$ and $t_{ASC} \leq t_{AA} - t_{CAC} - t_T$, access time is t_{AA} .
 - *9. Measured with a load equivalent to one TTL loads and 100 pF.
 - *10. t_{OFF} and t_{OEZ} is specified that output buffer change to high-impedance state.
 - *11. Operation within the $t_{RCD}(\max)$ limit ensures that $t_{RAC}(\max)$ can be met. $t_{RCD}(\max)$ is specified as a reference point only; if t_{RCD} is greater than the specified $t_{RCD}(\max)$ limit, access time is controlled exclusively by t_{CAC} or t_{AA} .
 - *12. $t_{RCD}(\min) = t_{RAH}(\min) + 2 t_T + t_{ASC}(\min)$.
 - *13. Operation within the $t_{RAD}(\max)$ limit ensures that $t_{RAC}(\max)$ can be met. $t_{RAD}(\max)$ is specified as a reference point only; if t_{RAD} is greater than the specified $t_{RAD}(\max)$ limit, access time is controlled exclusively by t_{CAC} or t_{AA} .
 - *14. Either t_{RRH} or t_{RCH} must be satisfied for a read cycle.
 - *15. t_{WCS} is specified as a reference point only. If $t_{WCS} \geq t_{WCS}(\min)$ the data output pin will remain High-Z state through entire cycle.
 - *16. Assumes that $t_{WCS} < t_{WCS}(\min)$.
 - *17. Either t_{DZC} or t_{DZO} must be satisfied.
 - *18. t_{CPA} is access time from the selection of a new column address (that is caused by changing \overline{CAS} from "L" to "H"). Therefore, if t_{CP} is long, t_{CPA} is longer than $t_{CPA}(\max)$.
 - *19. Assumes that \overline{CAS} -before- \overline{RAS} refresh.
 - *20. t_{WCS} , t_{CWD} , t_{RWD} , t_{AWD} , and t_{CPWD} are not restrictive operating parameters. They are included in the data sheet as an electrical characteristic only. If $t_{WCS} > t_{WCS}(\min)$, the cycle is an early write cycle and DQ pin will maintain high-impedance state throughout the entire cycle. If $t_{CWD} > t_{CWD}(\min)$, $t_{RWD} > t_{RWD}(\min)$, and $t_{AWD} > t_{AWD}(\min)$, the cycle is a read modify-write cycle and data from the selected cell will appear at the DQ pin. If neither of the above conditions is satisfied, the cycle is a delayed write cycle and invalid data will appear the DQ pin, and write operation can be executed by satisfying t_{RWL} , t_{CWL} , and t_{RAL} specifications.

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Fig. 2 – t_{RAC} vs. t_{RCD}

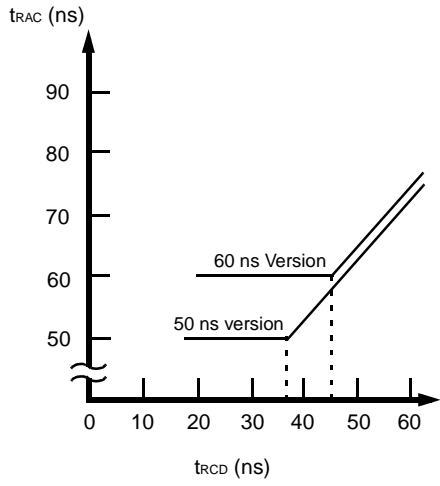


Fig. 3 – t_{RAC} vs. t_{RAD}

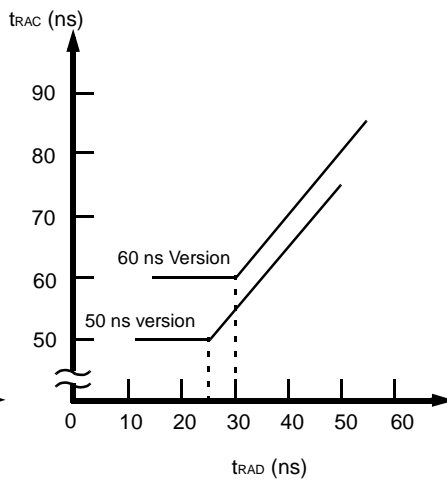
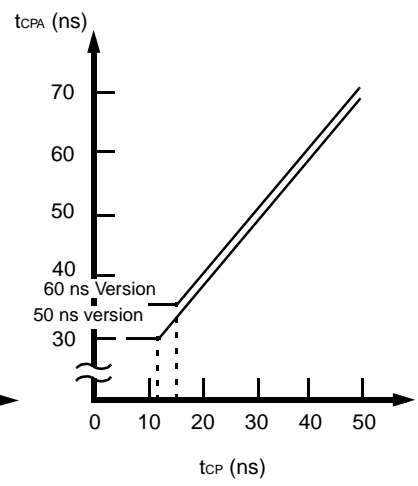
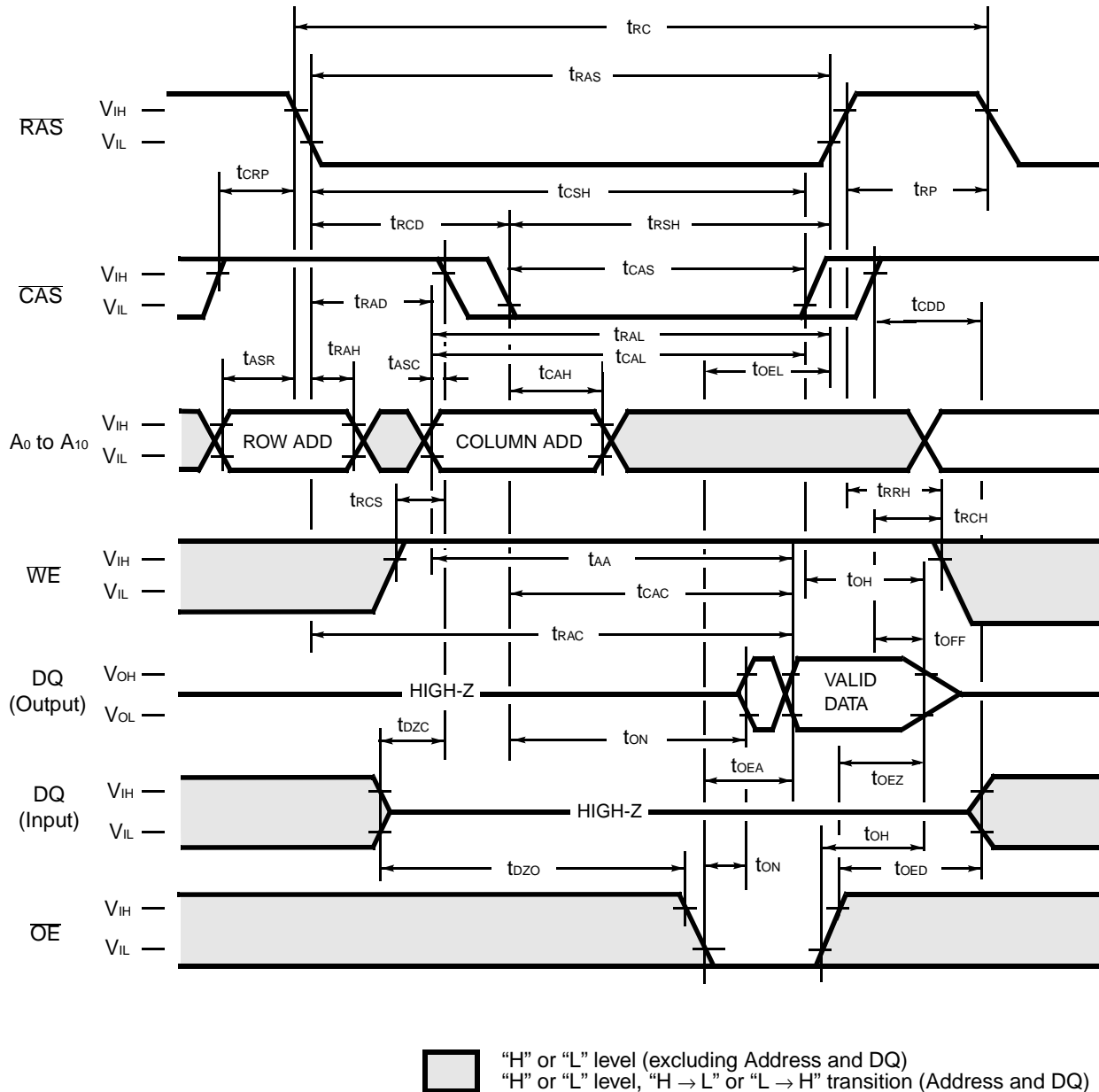


Fig. 4 – t_{CPA} vs. t_{CP}



MB81V17800B-50/-60/-50L/-60L

Fig. 5 – READ CYCLE

**DESCRIPTION**

To implement a read operation, a valid address is latched in by the \overline{RAS} and \overline{CAS} address strobes and with \overline{WE} set to a High level and \overline{OE} set to a low level, the output is valid once the memory access time has elapsed. The access time is determined by $RAS(t_{RAC})$, $CAS(t_{CAC})$, $OE(t_{OEA})$ or column addresses (t_{AA}) under the following conditions:

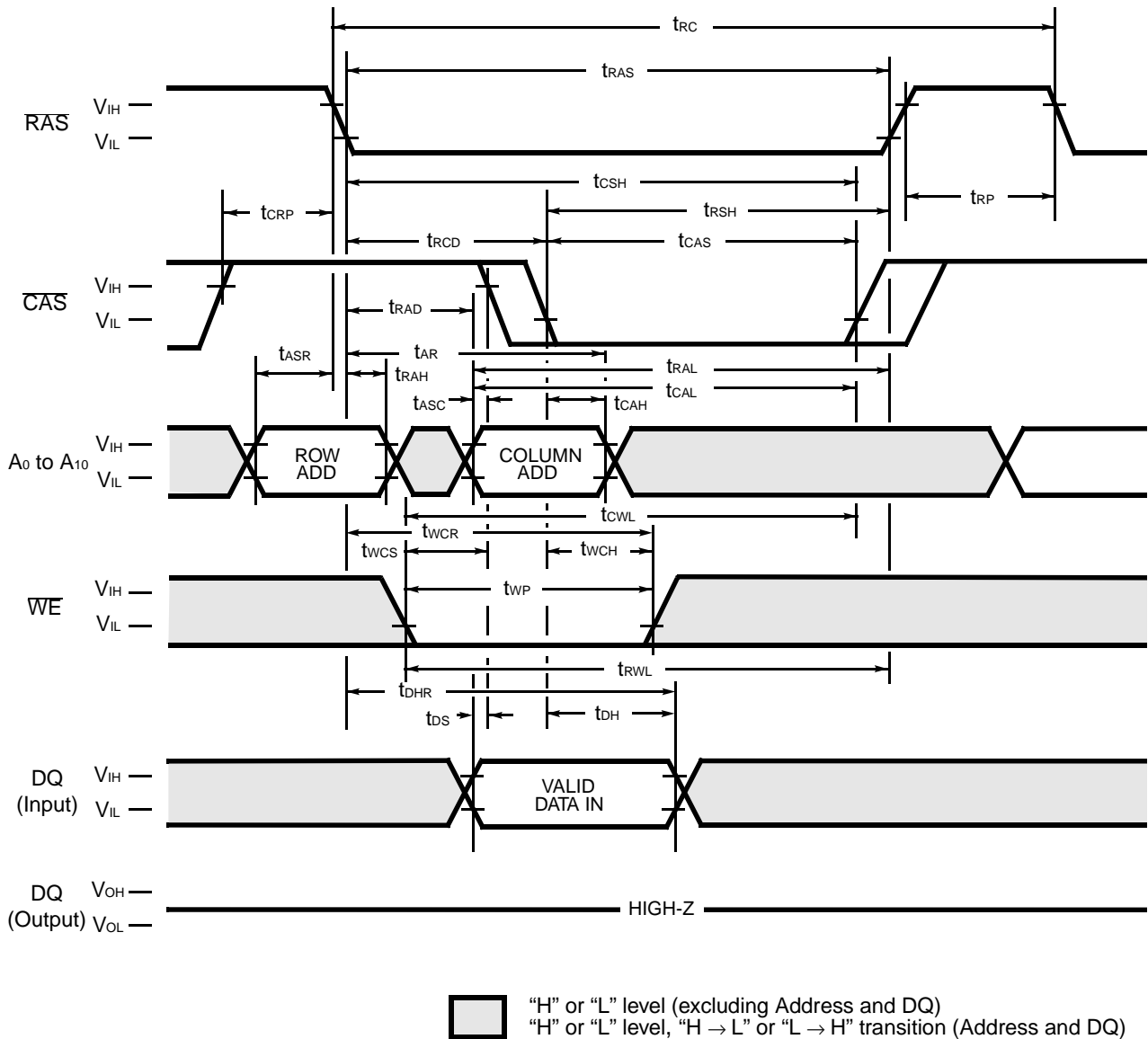
If $t_{RCD} > t_{RCD}(\max)$, access time = t_{CAC} .

If $t_{RAD} > t_{RAD}(\max)$, access time = t_{AA} .

If \overline{OE} is brought Low after t_{RAC} , t_{CAC} , or t_{AA} (whichever occurs later), access time = t_{OEA} .

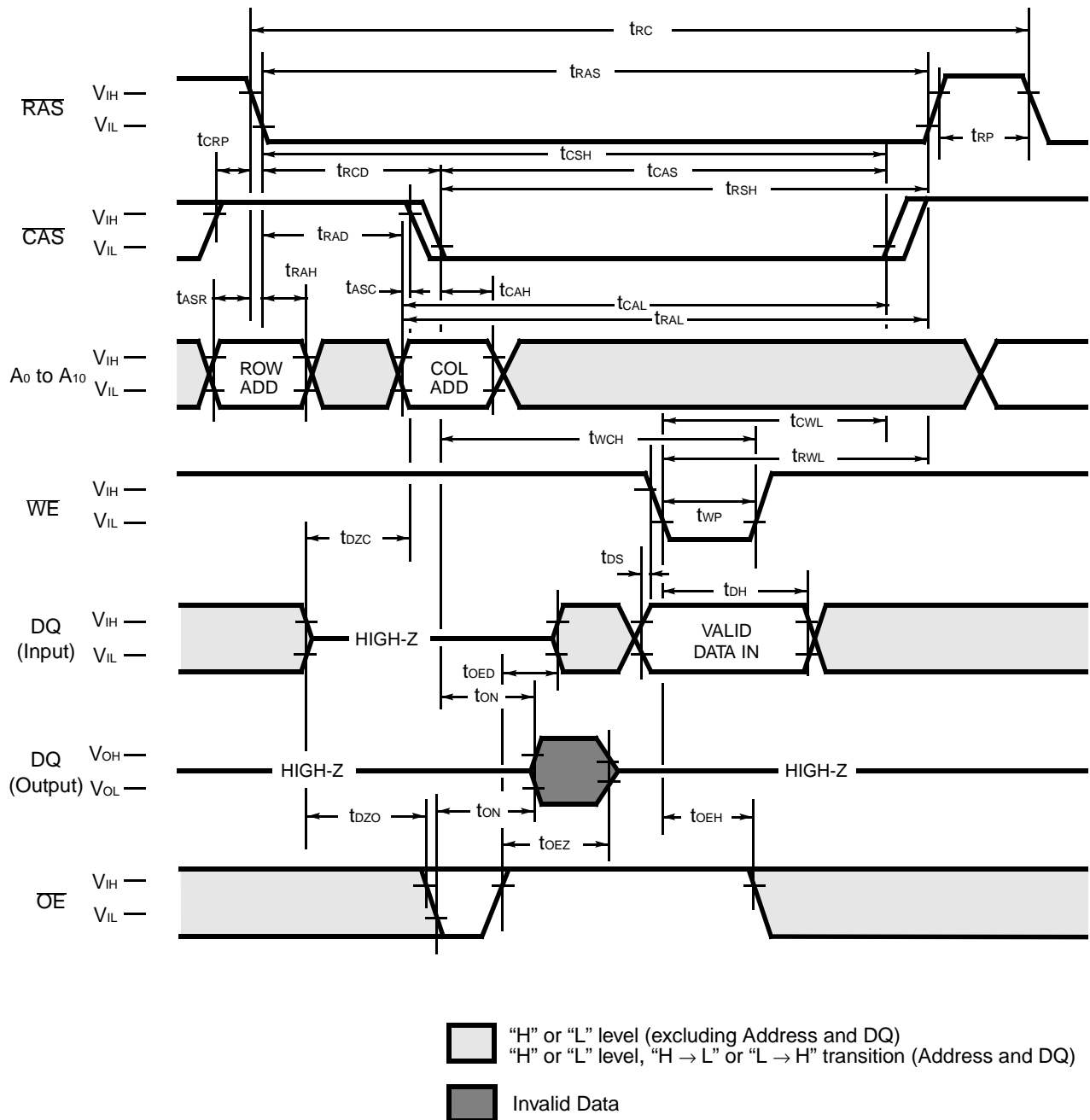
However, if either \overline{CAS} or \overline{OE} goes High, the output returns to a high-impedance state after t_{OH} is satisfied.

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Fig. 6 – EARLY WRITE CYCLE (\overline{OE} = “H” or “L”)**DESCRIPTION**

A write cycle is similar to a read cycle except \overline{WE} is set to a Low state and \overline{OE} is a "H" or "L" signal. A write cycle can be implemented in either of three ways—early write, \overline{OE} write (delayed write), or read-modify-write. During all write cycles, timing parameters t_{RWL} , t_{CWL} and t_{RAL} must be satisfied. In the early write cycle shown above t_{WCS} satisfied, data on the DQ pin is latched with the falling edge of CAS and written into memory.

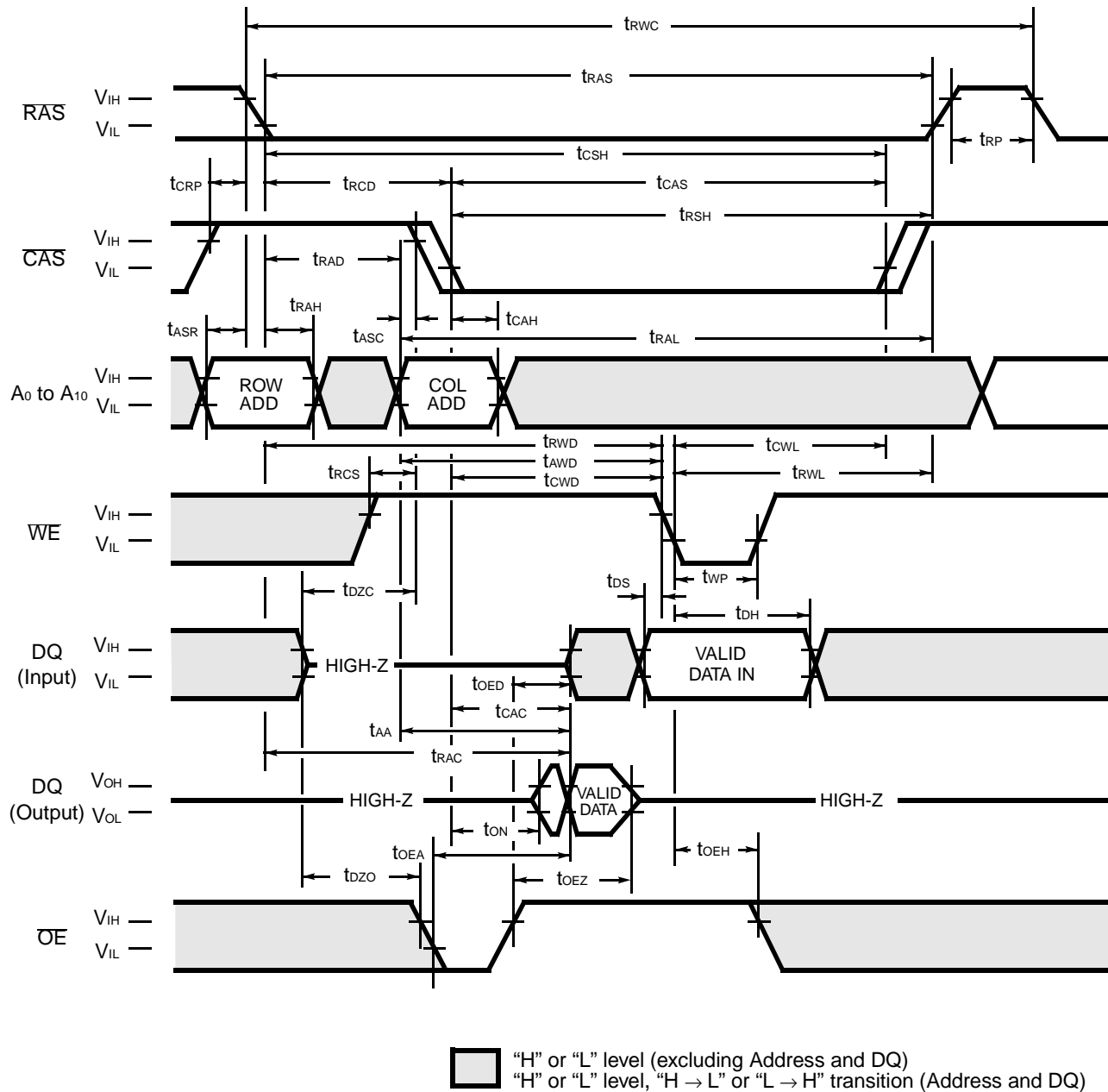
MB81V17800B-50/-60/-50L/-60L

Fig. 7 - DELAYED WRITE CYCLE (\overline{OE} control)**DESCRIPTION**

In the \overline{OE} (delayed write) cycle, t_{wcs} is not satisfied; thus, the data on the DQ pins is latched with the falling edge of \overline{WE} and written into memory. The Output Enable (\overline{OE}) signal must be changed from Low to High before \overline{WE} goes Low ($t_{oED} + t_{ds}$).

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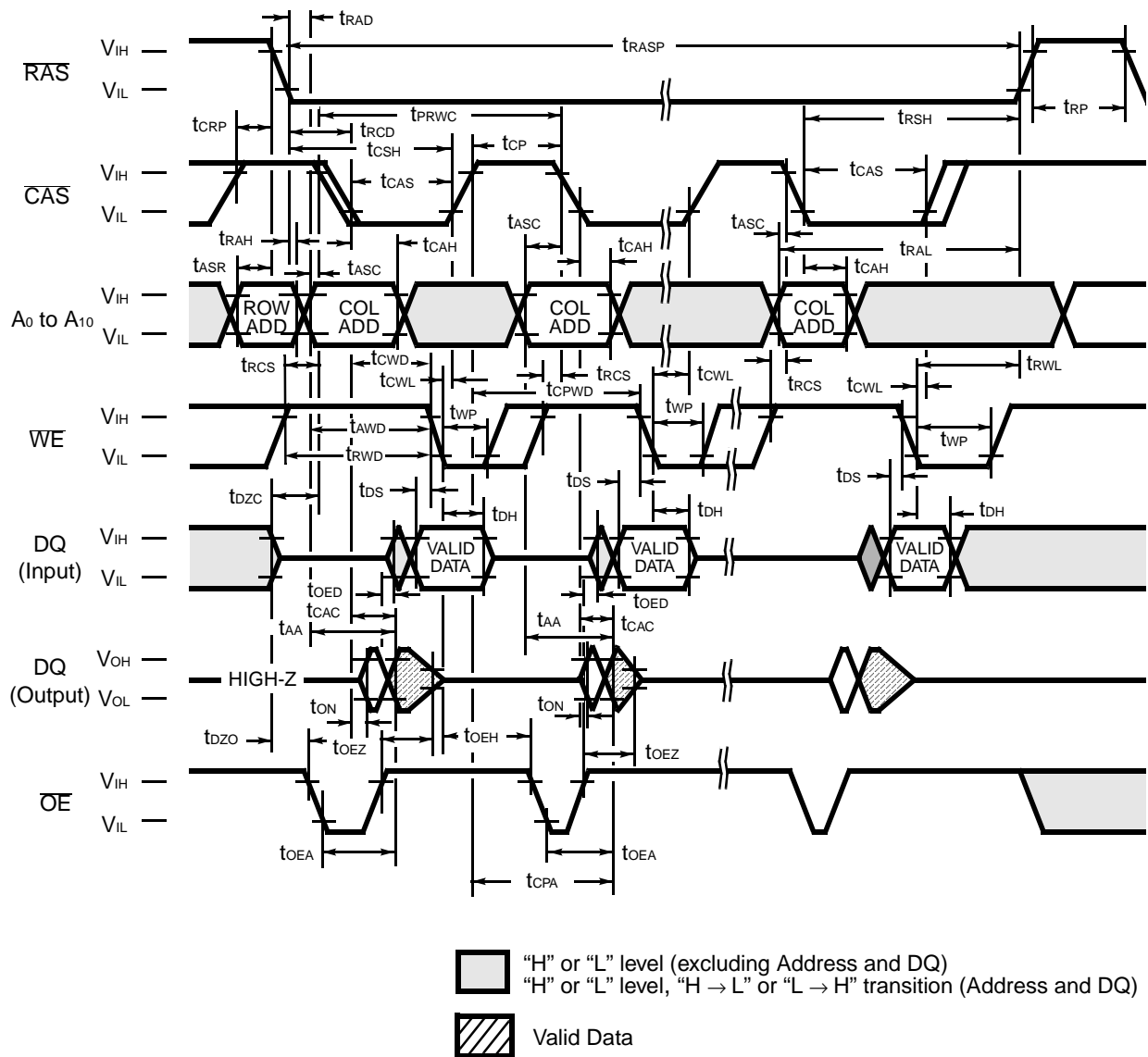
Fig. 8 – READ-MODIFY-WRITE-CYCLE

**DESCRIPTION**

The read-modify-write cycle is executed by changing \overline{WE} from High to Low after the data appears on the DQ pins. In the read-modify-write cycle, \overline{OE} must be changed from Low to High after the memory access time.

MB81V17800B-50/-60/-50L/-60L

Fig. 12 – FAST PAGE MODE READ-MODIFY-WRITE CYCLE

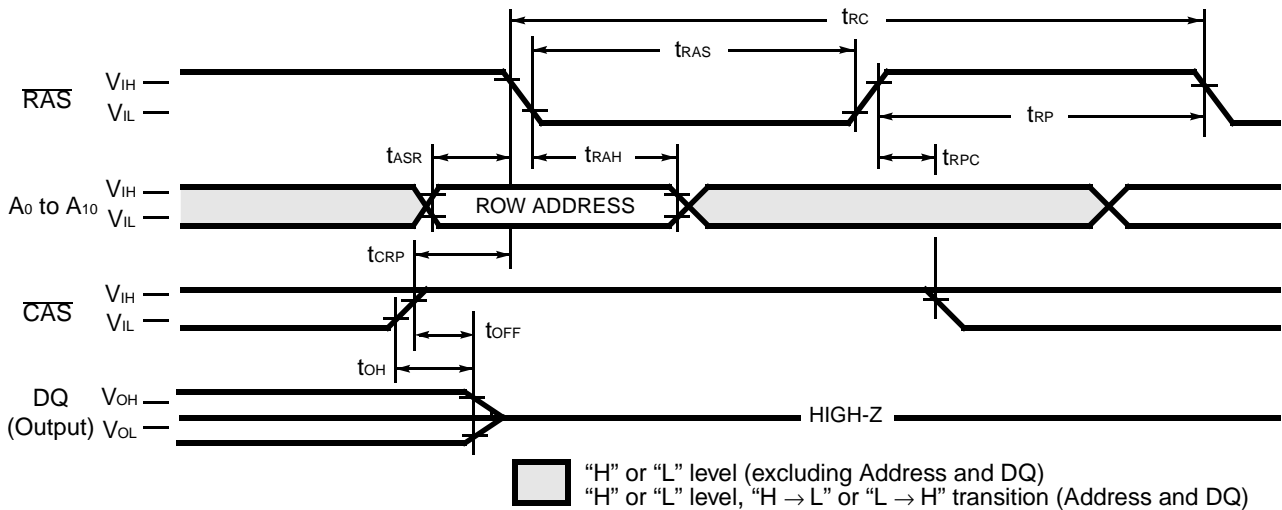


DESCRIPTION

During the fast page mode of operation, the read-modify-write cycle can be executed by switching \overline{WE} from High to Low after input data appears at the DQ pins during a normal cycle.

MB81V17800B-50/-60/-50L/-60L

Fig. 13 – RAS-ONLY REFRESH ($\overline{WE} = \overline{OE} = \text{"H" or "L"}$)

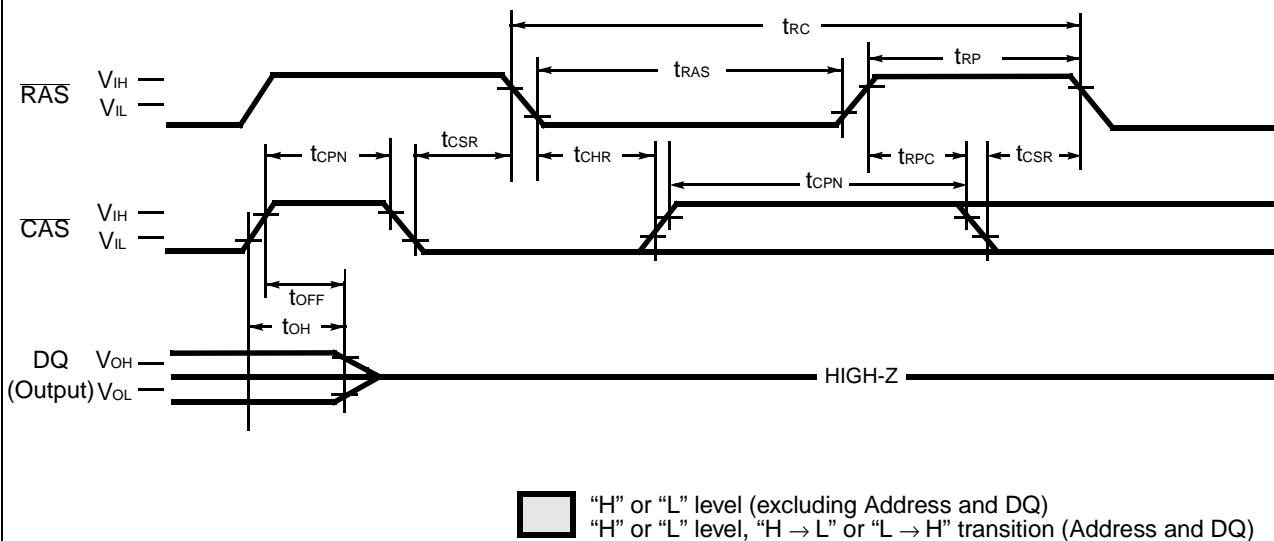


DESCRIPTION

Refresh of RAM memory cells is accomplished by performing a read, a write, or a read-modify-write cycle at each of 2048 row addresses every 32.8-milliseconds. Three refresh modes are available: RAS-only refresh, CAS-before-RAS refresh, and hidden refresh.

RAS-only refresh is performed by keeping RAS Low and CAS High throughout the cycle; the row address to be refreshed is latched on the falling edge of RAS. During RAS-only refresh, DQ pin is kept in a high-impedance state.

Fig. 14 – CAS-BEFORE-RAS REFRESH (ADDRESSES = $\overline{OE} = \text{"H" or "L"}$)

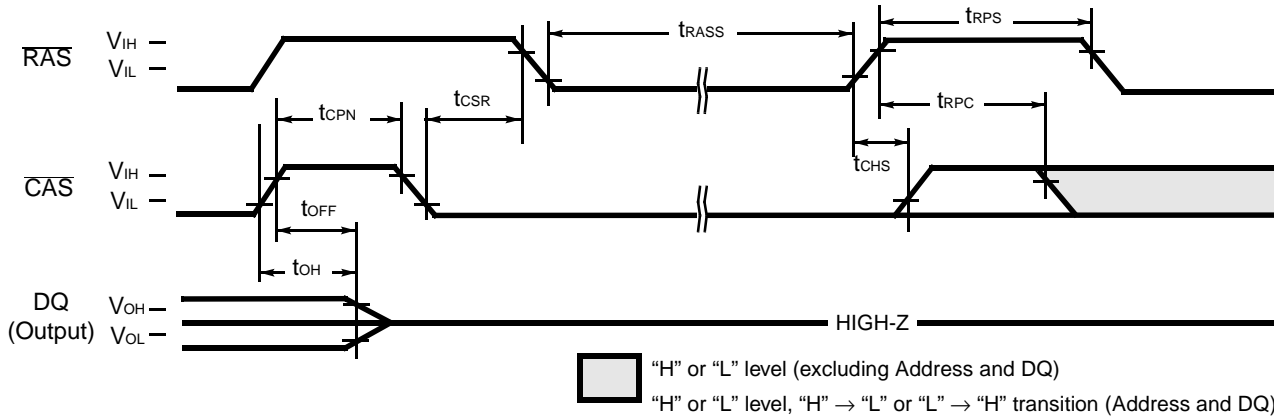


DESCRIPTION

CAS-before-RAS refresh is an on-chip refresh capability that eliminates the need for external refresh addresses. If CAS is held Low for the specified setup time (t_{CSR}) before RAS goes Low, the on-chip refresh control clock generators and refresh address counter are enabled. An internal refresh operation automatically occurs and the refresh address counter is internally incremented in preparation for the next CAS-before-RAS refresh operation.

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Fig. 17 - SELF REFRESH CYCLE (A_0 to $A_{10} = \overline{WE} = \overline{OE} = \text{"H" or "L"}$)



(At recommended operating conditions unless otherwise noted.)

No.	Parameter	Symbol	MB81V17800B-50L		MB81V17800B-60L		Unit
			Min.	Max.	Min.	Max.	
65	RAS Pulse Width	t_{RASS}	100	—	100	—	μs
66	RAS Precharge Time	t_{RPS}	90	—	110	—	ns
67	CAS Hold Time	t_{CHS}	-50	—	-50	—	ns

Note: Assumes Self Refresh cycle only.

DESCRIPTION

The self refresh cycle provides a refresh operation without external clock and external Address. Self refresh control circuit on chip is operated in the self refresh cycle and refresh operation can be automatically executed using internal refresh address counter.

If \overline{CAS} goes to "L" before \overline{RAS} goes to "L" (CBR) and the condition of \overline{CAS} "L" and \overline{RAS} "L" is kept for term of t_{RASS} (more than 100 μs), the device can enter the self refresh cycle. Following that, refresh operation is automatically executed at fixed intervals using internal refresh address counter during " $\overline{RAS}=\text{L}$ " and " $\overline{CAS}=\text{L}$ ".

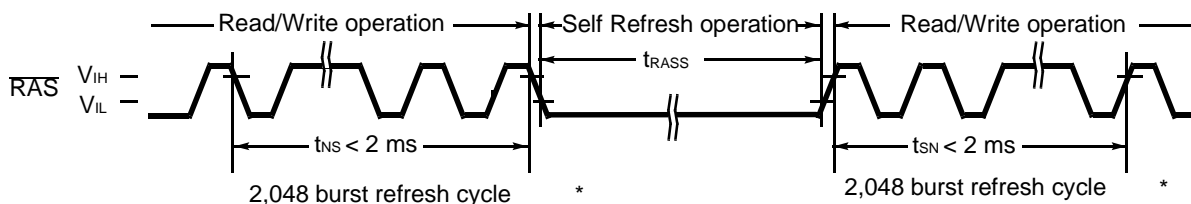
Exit from self refresh cycle is performed by toggling \overline{RAS} and \overline{CAS} to "H" with specified t_{CHS} min.. In this time, \overline{RAS} must be kept "H" with specified t_{RPS} min.

Using self refresh mode, data can be retained without external \overline{CAS} signal during system is in standby.

Restriction for Self Refresh operation ;

For self refresh operation, the notice below must be considered.

- 1) In the case that distributed CBR refresh are operated between read/write cycles
Self Refresh cycles can be executed without special rule if 2,048 cycles of distributed CBR refresh are executed within t_{REF} max.
- 2) In the case that burst CBR refresh or distributed/burst \overline{RAS} only refresh are operated between read/write cycles
2,048 times of burst CBR refresh or 2,048 times of burst \overline{RAS} only refresh must be executed before and after Self Refresh cycles.



* Read/Write operation can be performed non refresh time within t_{NS} or t_{SN}

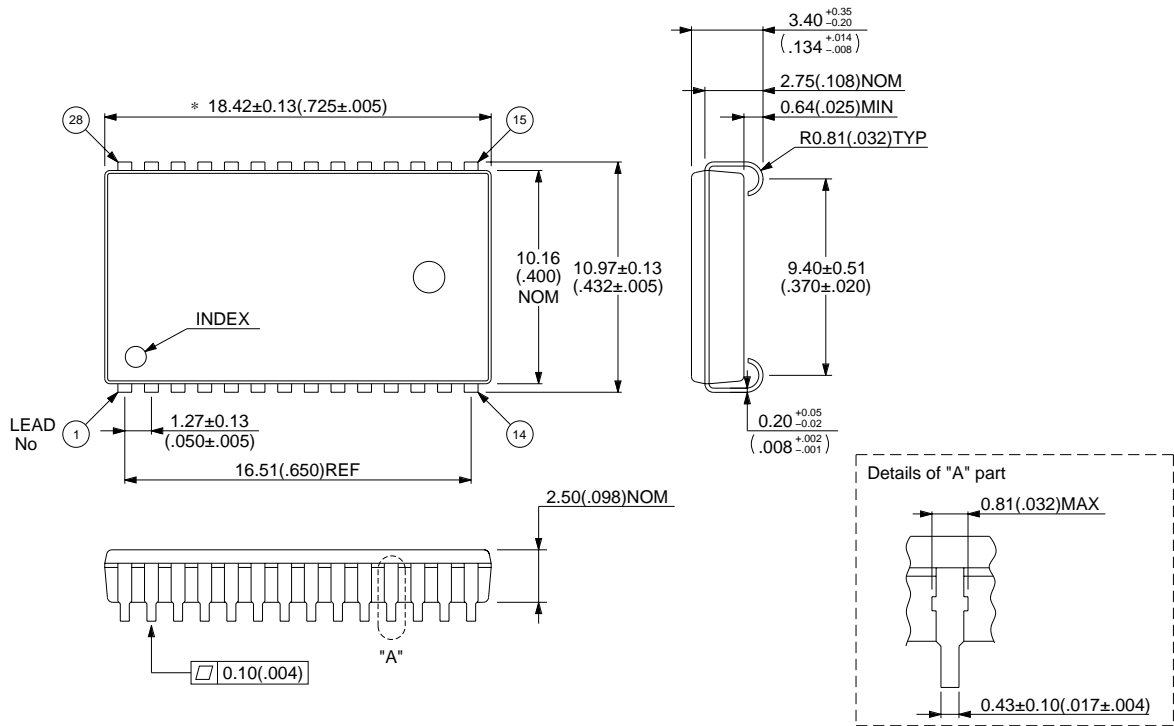
MB81V17800B-50/-60/-50L/-60L

PACKAGE DIMENSIONS

(Suffix: -PJ)

28-pin plastic SOJ
(LCC-28P-M07)

*: Resin protrusion. (Each side: .015 (.006) MAX)



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Dimensions in mm (inches)

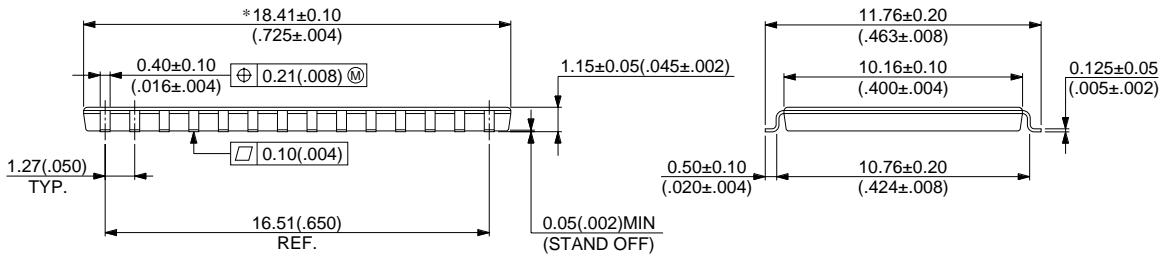
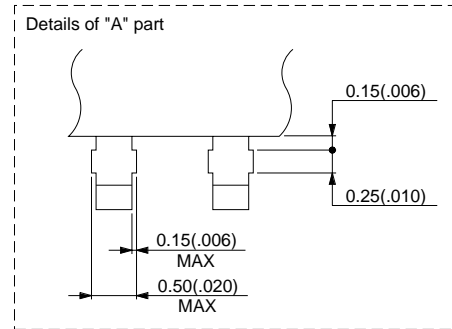
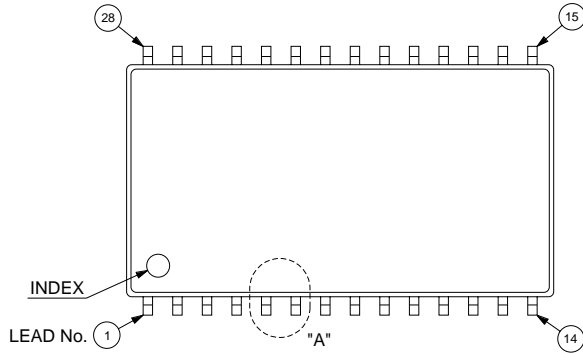
MB81V17800B-50/-60/-50L/-60L

(Continued)

(Suffix: -PFTN)

28-pin plastic TSOP (II)
(FPT-28P-M14)

*: Resin protrusion. (Each side: .015(.006) MAX)



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Dimensions in mm (inches)

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